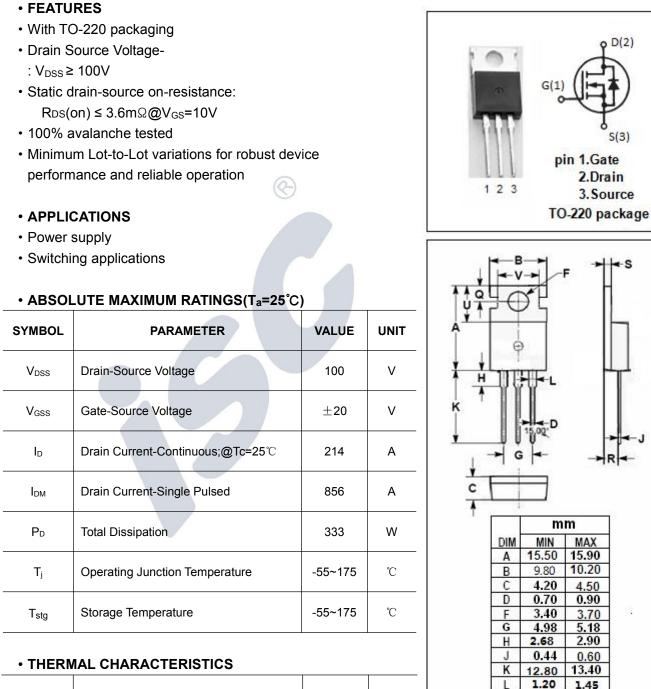


INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

FDP036N10A



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SYMBOL	PARAMETER	МАХ	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	0.45	°C /W

isc & iscsemi is registered trademark

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2.70

2.30

1.29

6.45

8.66

2.90

2.70

1.35

6.65

8.86



isc N-Channel MOSFET Transistor

FDP036N10A

ELECTRICAL CHARACTERISTICS

$T_{\text{C}}\text{=}25^{\circ}\!\!\!\!\!\mathrm{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D = 250uA	100			V
V _{GS} (th)	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =250uA	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 75A			3.6	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V;V _{DS} = 0V			±100	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 80V; V _{GS} = 0V V _{DS} = 80V; V _{GS} = 0V;T _J =150°C			1 500	μA
VSDF	Diode forward voltage	I _{SD} = 75A, V _{GS} = 0 V			1.25	V

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